Abstracts

Extraction Based Model for GaAs MESFET Switches

A. Ehoud, L.P. Dunleavy, S.C. Lazar and R.E. Branson. "Extraction Based Model for GaAs MESFET Switches." 1994 MTT-S International Microwave Symposium Digest 94.2 (1994 Vol. II [MWSYM]): 861-864.

A simple method for extracting equivalent circuit parameters for series and shunt GaAs FET switches was developed. To the authors knowledge, this is the first reported extraction based model for MMIC compatible switches. The circuit elements are extracted from one set of S-parameter measurements, and scale with gate geometry. Good agreement is shown between simulated and model results for 0.5 µm by 300 µm series and shunt GaAs FET switches across the 0.45 - 26.5 GHz band.

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